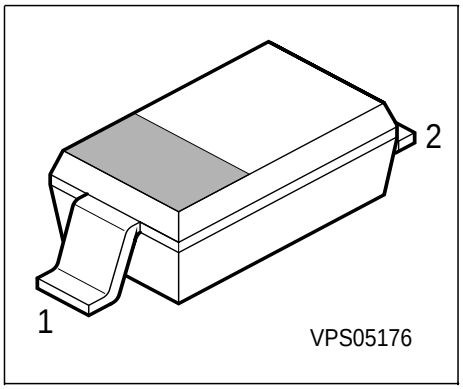
Silicon Schottky Diode

- Rectifier Schottky diode with extreme low V_F drop for mobile communication
- For power supply
- For clamping and proptection in low voltage application
- For detection and step-up-conversion



ESD: **E**lectro**s**tatic **d**ischarge sensitive device, observe handling precaution!

Type	Marking	Ordering Code	Pin Configuration		Package
BAT 60A	white/3	Q62702-A1188	1 = C	2 = A	SOD-323

Maximum Ratings

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	10	V
Forward current	I_F	3	A
Surge forward current (t< 100µs)	I_{FSM}	5	mA
Total power dissipation, T_S = 28 °C	P_{tot}	1350	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	- 55 ...+150	

Maximum Ratings

Junction - ambient 1)	R_{thJA}	≤ 160	K/W
Junction - soldering point	R_{thJS}	≤ 90	

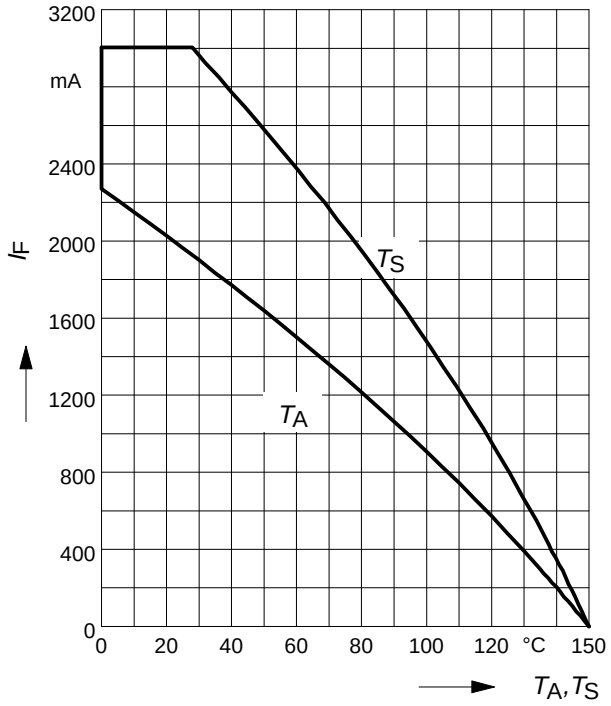
1) Package mounted on epoxy pcb 40mm x 40mm x 1.5mm / 0.5cm^2 Cu

Electrical Characteristics at T_A = 25 °C, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC characteristics					
Reverse current	I_R				mA
V_R = 5 V		-	0.3	-	
V_R = 8 V		-	0.45	-	
Reverse current	I_R	-	18	-	µA
V_R = 8 V, T_A = 80 °C					
Forward voltage	V_F				V
I_F = 10 mA		-	0.12	-	
I_F = 100 mA		-	0.2	-	
I_F = 1000 mA		-	0.3	-	
AC characteristics					
Diode capacitance	C_T	-	20	-	pF
V_R = 5 V, f = 1 MHz					

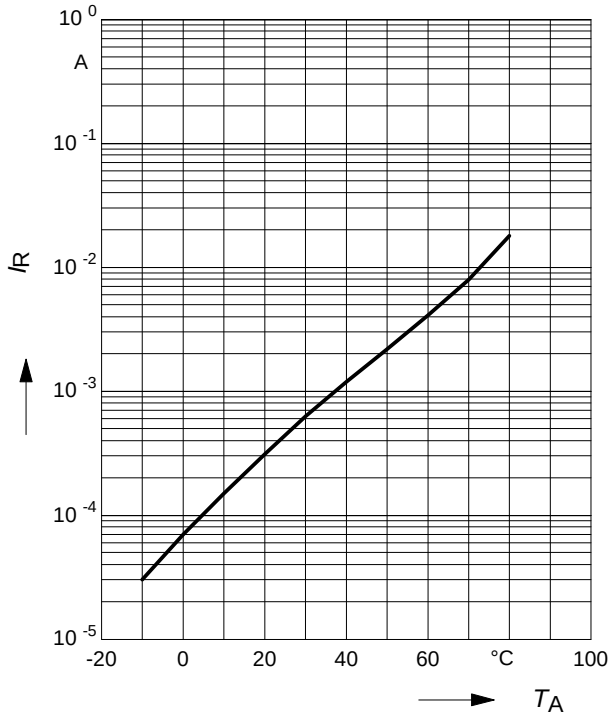
Forward current $I_F = f(T_A^*; T_S)$

* Package mounted on epoxy

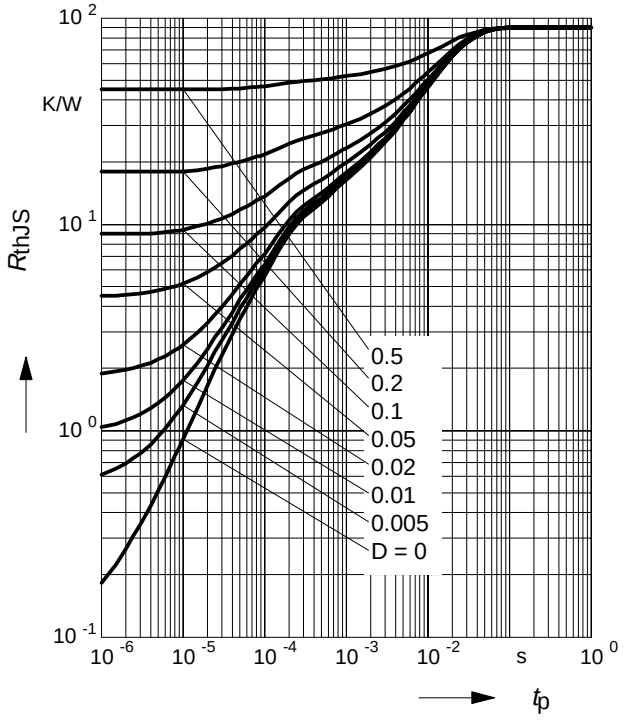


Reverse current $I_R = f(T_A)$

V_R = 8V



Permissible Pulse Load $R_{thJS} = f(t_p)$



Permissible Pulse Load

$I_{Fmax} / I_{FDC} = f(t_p)$

